

Day 1 (Monday, July 7)		Room Titane 2
Session 1 – Remote and van der Waals epitaxy		
		Chair: Sanghoon Bae
Time	Speaker	Title
08:15 – 08:20	Bérangère Hyot CEA, Leti	Welcome
08:20 – 08:30	Thomas Ernst CEA, Leti	Introduction and Welcome
08:30 – 09:10	Ionut Radu SOITEC, France	Single-crystalline thin films à la carte: applications and technology opportunities
09:10 – 09:30	Kyusang Lee Future Semiconductor Business, USA	From Laboratory to Industry: Remote Epitaxy for Scalable Semiconductor Membranes
09:30 – 09:50	Hyunseok Kim University of Illinois Urbana-Champaign, USA	Is remote epitaxy really remote? – Unveiling the mode of epitaxy on 2D materials
09:50 – 10:05	Coffee Break (15 min)	

Session 2 – Monolithic 3D integrations		
		Chair: Munho Kim
Time	Speaker	Title
10:05 – 10:45	Jeehwan Kim MIT (Massachusetts Institute of Technology), USA	Seamless wafer-free monolithic 3D integration enabled by confined growth and remote epitaxy
10:45 – 11:15	Saptarshi Das Penn State University, USA	2D Materials for 3D Integration, Advanced Logic, and More
11:15 – 11:45	Qing Cao University of Illinois Urbana-Champaign, USA	Monolithic three-dimensional integration of complementary single-crystalline silicon transistors
11:45 – 12:05	Jiho Shin TAMU (Texas A&M University), USA	Dissolvable, Flexible, and 3D-integrated electronics using freestanding membranes
12:05 – 13:35	Lunch Break (90 min)	

Session 3&4 – Remote and van der Waals epitaxy		
		Chair: Jian Shi & Berangere HYOT
Time	Speaker	Title
13:35 – 14:15	Chang-Beom Eom University of Wisconsin-Madison, USA	Twisted oxide membrane interface by local atomic registry design
14:15 – 14:45	Young Joon Hong SKKU (Sungkyunkwan University), South Korea	Nitride-based MOCVD remote epitaxy for high-performance device applications
14:45 – 15:05	Hyun S. Kum Yonsei University, South Korea	Rapid low-temperature formation of graphene-coated SiC substrates for remote and vdW epitaxy
15:05 – 15:35	Jian Shi RPI (Rensselaer Polytechnic Institute), USA	Electrical and Optoelectronic Phenomena at van der Waals 2D–3D Phase-Transition Compound Interfaces
15:35 – 16:05	Abdallah Ougazzaden Georgia Institute of Technology, EU	2D hBN in GaN Optoelectronics: Dual Roles in Epitaxial Engineering and Device Innovation.
16:05 – 16:25	Coffee Break (15 min)	

Panel Discussion - Meet the Editors		
Time	Panel	Topic
16:30 – 17:15	Karl Ziemelis (Nature, Chief Applied & Physical Sciences Editor) Mathew Parker (Nature Electronics) Olga Bubnova (Nature Sensors)	Open disscussion with panels, organizers, and attendees

Poster Session	
Time	
17:15 – 18:15	Poster Session
18:15 – 20:00	Wine and Cheese Tasting

Day 2 (Tuesday, July 8)		Room Titane 2	
Session 5 – Remote and van der Waals epitaxy			
Chair: Hyun S. Kum			
Time	Speaker	Title	
09:10 – 09:30	Sungkyu kim Sejong University, South Korea	0	
09:30 – 09:50	Celesta Chang SNU (Seoul National University), South Korea	Visualizing freestanding membranes in 3D by electron ptychography	
09:50 – 10:10	Wei Kong Westlake University, USA	Interfacial Mechanisms of Single-crystalline MoS2 on Sapphire	
10:10 – 10:30	Takuji Maekawa ROHM Co., Ltd., Japan	Fabrication of SiC remote epitaxial membranes for wafer cost reduction	
10:30 – 10:45	Coffee Break (15 min)		

Session 7 – Growth and Applications of membrane		
Chair: Jiho Shin		
Time	Speaker	Title
10:45 – 11:05	Tobias Henksmeier Paderborn University, Germany	Remote Epitaxy of III-V films on monolayer amorphous carbon covered substrates
11:05 – 11:25	Jinkyong Yoo Los Alamos National Laboratory, USA	0
11:25 – 11:45	Yoshitaka Taniyasu NTT Basic Research Laboratories, Japan	MOCVD growth of 1D structures based on group III–VI layered semiconductors
11:45 – 12:05	Yuta Saito Tohoku University, Japan	Growth and Synthesis of layered tellurides for field effect transistor application
12:05 – 12:25	Pavan Nukala IISc (Indian Institute of Science), India	Device quality epitaxial ferroelectric oxides obtained through various layer transfer techniques
Lunch Break (80 min)		

Session 9 – Monolithic 3D integrations		
Chair: Saptarshi Das		
Time	Speaker	Title
13:45 – 14:15 Keynote	Didier Landru SOITEC	Membranes manufacturing with SOI & SmartCut™ technology
14:15 – 14:45 Keynote	Perrine Batude Leti	Status on 3D sequential integration with low temperature stacked Silicon devices
14:45 – 15:05	Kyusang Lee UVA (University of Virginia), USA	CMOS + X towards edge intelligence
15:05 – 15:25	Jianshi Tang Tsinghua University, Beijing, China	Monolithic 3D Integration with BEOL-Compatible Materials and Devices for Energy-Efficient Computing-in-Memory
15:25 – 15:55 Keynote	Sang-Hoon Bae Washington University in St. Louis, USA	Materials Innovation through 2D materials and 3D nanomembranes: From artificial heterostructures to M3D integration
15:55 – 16:15	Coffee Break (20 min)	

16:15 – 18:15	Showroon visit
---------------	----------------

18:15 – 19:00	Refresments
---------------	-------------

18:15 – 22:30	Gala Dinner Conference dinner at Château de la Commanderie (for Oral presenters, Panelists, and Organizers.) (There will be a shuttle bus from Minatec to Château de la Commanderie)
---------------	---

Day 2 (Tuesday, July 8)		Room Chrome 1	
Session 6 – Synthesis and Applications of 2D materials			
			Chair: Jinkyong Yoo
Time	Speaker	Title	
08:30 – 09:10 Plenary	Jiwoong Park University of Chicago, USA	More Magic with 2D Materials	
09:10 – 09:30	Ying-Hao Eddie Chu National Tsing Hua University, Taiwan	Van der Waals heteroepitaxy of Bi2O2X (X=S, Se, Te).	
09:30 – 09:50	Kibum Kang KAIST (Korea Advanced Institute of Science & Technology), South Korea	Towards Ultimate Nucleation-Control in 2D Film Growth	
09:50 – 10:10	Adrien Michon CNRS-CRHEA, France	Self-limited monolayer graphene growth on SiC with propane-hydrogen CVD	
10:10 – 10:30	Varun Harbola Max Planck Insitute, Germany	Heterointegration and interface design beyond epitaxy	
10:30 – 10:45	Coffee Break (15 min)		

Session 8 – Applications of free-standing membranes		
Chair: Kyusang Lee		
Time	Speaker	Title
10:45 – 11:15	Nanshu Lu	Graphene E-Tattoos
Keynote	UT-Austin (University of Texas-Austin), USA	
11:15 – 11:45	Nini Pryds	Oxide Membranes: Fabrication, Transfer, and Stacking – Current Advances and Future Outlook
Keynote	DTU (Technical Univeristy of Denmark), Denmark	
11:45 – 12:05	Minjoo Larry Lee	0
	University of Illinois Urbana-Champaign, USA	
12:05 – 12:25	Abderraouf Boucherif	Engineering Flexible Nanomembranes Using Porous Semiconductors and Graphene
	Université de Sherbrooke, Canada	
12:25 – 12:45	Junwoo Son	Single-crystalline rutile oxide nanomembranes: a versatile platform to overcome lattice mismatch
	Seoul National University (SNU), South Korea	
12:45 – 13:45	Lunch Break (60 min)	

Session 10 – Synthesis and Applications of 2D materials		
Chair: Celesta Chang		
Time	Speaker	Title
13:45 – 14:15 Keynote	Deji Akinwande UT-Austin (University of Texas-Austin), USA	2D materials for hydrogen fuel cells and clean energy
14:15 – 14:45 Keynote	Lain-Jong Li National University of Singapore, Singapore	The Potential of Transition Metal Dichalcogenides for Low-Power Electronics: CFET Demonstration
14:45 – 15:05	Salim El Kazzi AIXTRON	Enabling Next-Gen 3D Integration via Wafer-Scale Epitaxy on 2D Materials
15:05 – 15:25	He Ding BIT (Bejing Institute of Technology), China	Ripple-free, high-performance DC voltage converter based on integrated optoelectronic devices
15:25 – 15:45	Sanghoon Chae Nanyang Technological University (NTU), Singapore	Electrically Tunable Nonlinear Photonics using Ferroelectric 2D Materials Integration
15:45 – 16:05	Coffee Break (20 min)	

Day 3 (Wednesday, July 9)		Room Titane 2	
Session 11 – Applications of free-standing membranes			
Chair: Hyunseok Kim			
Time	Speaker	Title	
09:10 – 09:50 Plenary	Sheng Xu University of California San Diego, USA	Controlled epitaxial growth and fabrication of hybrid halide perovskite membranes	
09:50 – 10:20 Keynote	Dong-Seon Lee GIST (Gwangju Institute of Science and Technology), South Korea	0	
10:20 – 10:40	Yun Seog Lee SNU (Seoul National University), South Korea	Freestanding Solid-Electrolyte Membranes for High-Energy-Density All-Solid-State Batteries.	
10:40 – 11:00	Fabien Chabuel CEA, Leti	CEA Leti general presentation	
11:00 – 11:35		Coffee Break (35 min)	

Session 13 – Applications of free-standing membranes		
Chair: Yun Seog Lee		
Time	Speaker	Title
11:35 – 11:55	Ning Li Penn State University, USA	Benchmarking phase change memory for analog in-memory computing
11:55 – 12:15	Yimo Han Rice University, USA	Strain and strain relaxation in van der Waals epitaxy revealed by advanced electron microscopy. (online)
12:15 – 12:35	Haozhe Wang Duke University, USA	Foundation Model Agent for 2D Materials Characterization (online)
12:35 – 14:05	Lunch Break (90 min)	

Day 3 (Wednesday, July 9)		Room Chrome 1	
Session 12 – Synthesis and Applications of 2D materials			
Chair: MunHo Kim			
Time	Speaker	Title	
09:10 – 09:30	Hanako Okuno CEA-Irig, France	4D-STEM : A new approach to studying large-scale 2D materials synthesized for device applications	
09:30 – 09:50	Yui Ogawa NTT Basic Research Laboratories, Japan	Investigation of the Growth Mechanism of Graphene in CVD Process via In-Situ Ultraviolet Optical Observation	
09:50 – 10:10	Matthieu Jamet CEA-Spintec, France	Large area epitaxial van der Waals heterostructures: new materials for tunable spintronic THz emission	
11:00 – 11:35			
Coffee Break (45 min)			

Session 14 – Applications of free-standing membranes		
Chair: Wei Kong		
Time	Speaker	Title
11:35 – 11:55	Jens Martin Leibniz Institute, Germany	Fabrication pathways for freestanding oxide membranes and novel crystalline interfaces
11:55 – 12:15	Matthew Lefevre Nayang Technological University (NTU), Singapore	Characterizing the electronic properties of graphene on silicon carbide via Atomic Force Microscopy”
12:15 – 12:35	MunHo Kim Nanyang Technological University (NTU), Singapore	Nanostructured Inorganic Wide Bandgap Semiconductors for Advanced Ultraviolet
12:35 – 14:05	Lunch Break (90 min)	

Closing Remark			
----------------	--	--	--